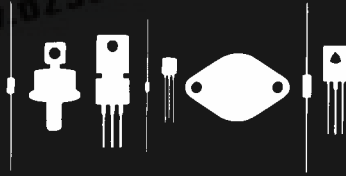


Central
Semiconductor Corp.
**Central
Semiconductor Corp.**
**CentralTM
Semiconductor Corp.**
145 Adams Avenue
Hauppauge, New York 11788



CQ220-10B
CQ220-10D
CQ220-10M
CQ220-10N

10 AMP TRIAC
200 THRU 800 VOLTS
JEDEC TO-220AB CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR CQ220-10B series type is an Epoxy Molded Silicon Triac designed for full wave AC control applications featuring gate triggering in all four (4) quadrants.

MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

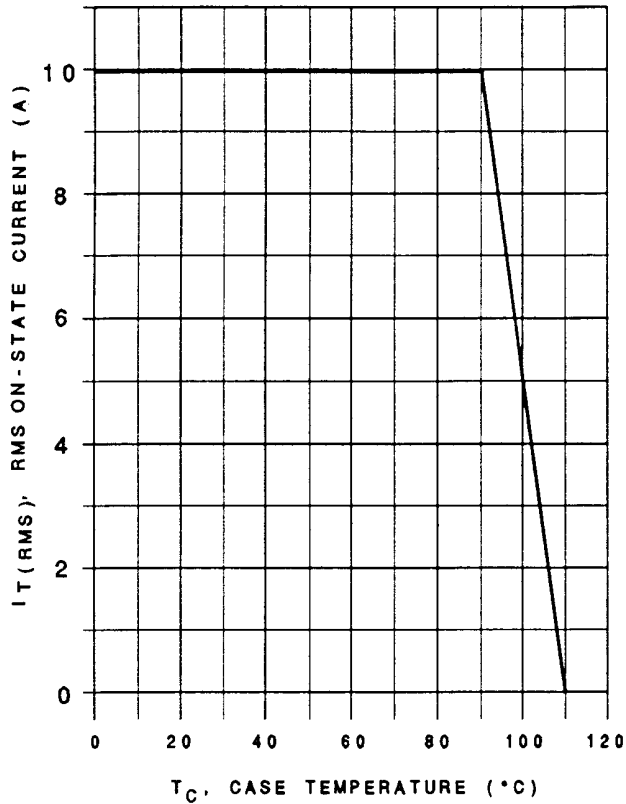
	SYMBOL	CQ220 -10B	CQ220 -10D	CQ220 -10M	CQ220 -10N	UNITS
Peak Repetitive Off-State Voltage	V _{DRM}	200	400	600	800	V
RMS On-State Current (T _C = 90°C)	I _{T(RMS)}			10		A
Peak One Cycle Surge (t = 10ms)	I _{TSM}			100		A
I ² t Value for Fusing (t = 10ms)	I ² _t			50		A ² s
Peak Gate Power (tp = 10μs)	P _{GM}			40		W
Average Gate Power Dissipation	P _{G(AV)}			1.0		W
Peak Gate Current (tp = 10μs)	I _{GM}			4.0		A
Peak Gate Voltage (tp = 10μs)	V _{GM}			16		V
Critical Rate of Rise of On-State Current						
Repetitive (F = 50Hz)	di/dt			10		A/μs
Storage Temperature	T _{stg}		-40 to +150			°C
Junction Temperature	T _J		-40 to +110			°C
Thermal Resistance	θ _{J-A}			60		°C/W
Thermal Resistance	θ _{J-C}			3.1		°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

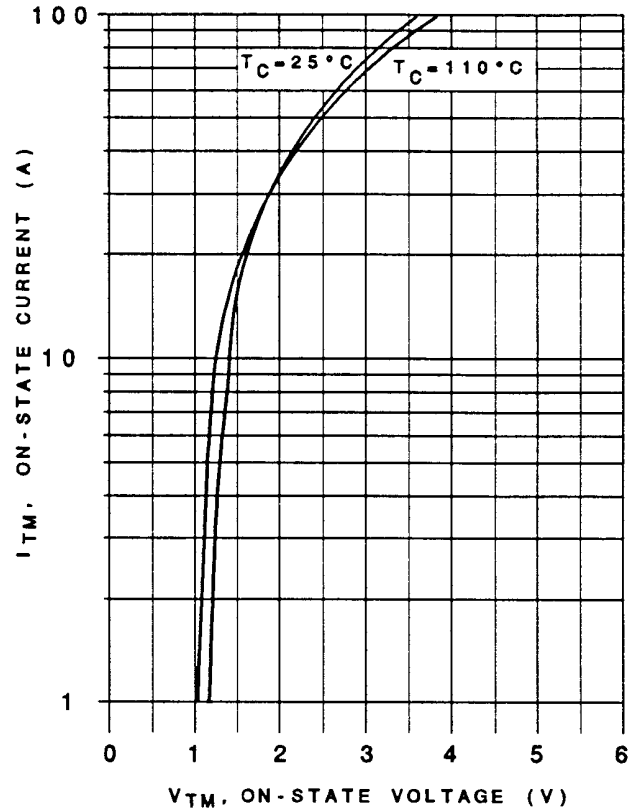
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _{DRM}	Rated V _{DRM}			0.01	mA
I _{DRM}	Rated V _{DRM} , T _C = 110°C			0.50	mA
I _{GT}	V _D = 12V, R _L = 33Ω, QUAD I,II,III			25	mA
I _{GT}	V _D = 12V, R _L = 33Ω, QUAD IV			50	mA
I _H	I _T = 100mA			25	mA
V _{GT}	V _D = 12V, R _L = 33Ω, QUAD I,II,III,IV			1.50	V
V _{TM}	I _{TM} = 14A, tp = 10ms			1.50	V
dv/dt	V _D = 2/3 V _{DRM} , R _{GK} = ∞, T _C = 110°C	100			V/μs

CQ220-10B SERIES RATING AND CHARACTERISTIC CURVES

RMS ON-STATE CURRENT vs. CASE TEMPERATURE



MAXIMUM ON-STATE CHARACTERISTICS



MECHANICAL DIMENSIONS

All Dimensions in Inches (mm).

